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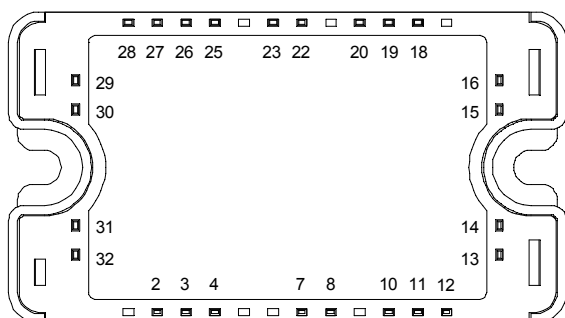
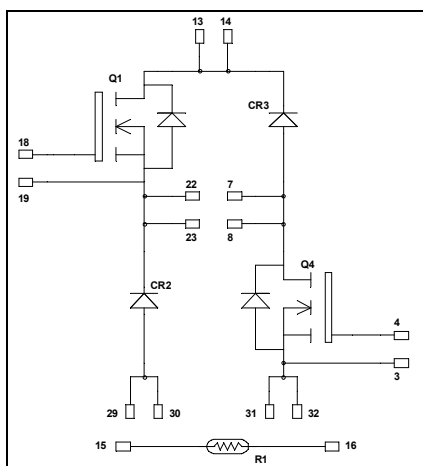


Asymmetrical - Bridge MOSFET Power Module

$$V_{DSS} = 500V$$

$$R_{DSon} = 65m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 51A \text{ @ } T_c = 25^\circ C$$



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23...

Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Power MOS 8™ MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	51
		$T_c = 80^\circ C$	38
I_{DM}	Pulsed Drain current	270	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	78	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	390
I_{AR}	Avalanche current (repetitive and non repetitive)	42	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}$ $V_{GS} = 0\text{V}$			250	μA
		$T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 42\text{A}$		65	78	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		10800		pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		1164		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		148		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$		340		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250\text{V}$		75		
Q_{gd}	Gate – Drain Charge	$I_D = 42\text{A}$		155		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 333\text{V}$ $I_D = 42\text{A}$ $R_G = 2.2\Omega$		60		ns
T_r	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			155		
T_f	Fall Time			50		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$			250	μA
		$T_j = 125^\circ\text{C}$			500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		60		A
V_F	Diode Forward Voltage	$I_F = 60\text{A}$		1.7	2.3	V
		$I_F = 120\text{A}$		2		
		$I_F = 60\text{A}, T_j = 125^\circ\text{C}$		1.4		
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}, T_j = 25^\circ\text{C}$		70		ns
		$V_R = 400\text{V}, T_j = 125^\circ\text{C}$		140		
Q_{rr}	Reverse Recovery Charge	$T_j = 25^\circ\text{C}, di/dt = 200\text{A}/\mu\text{s}$		100		nC
		$T_j = 125^\circ\text{C}$		690		

Thermal and package characteristics

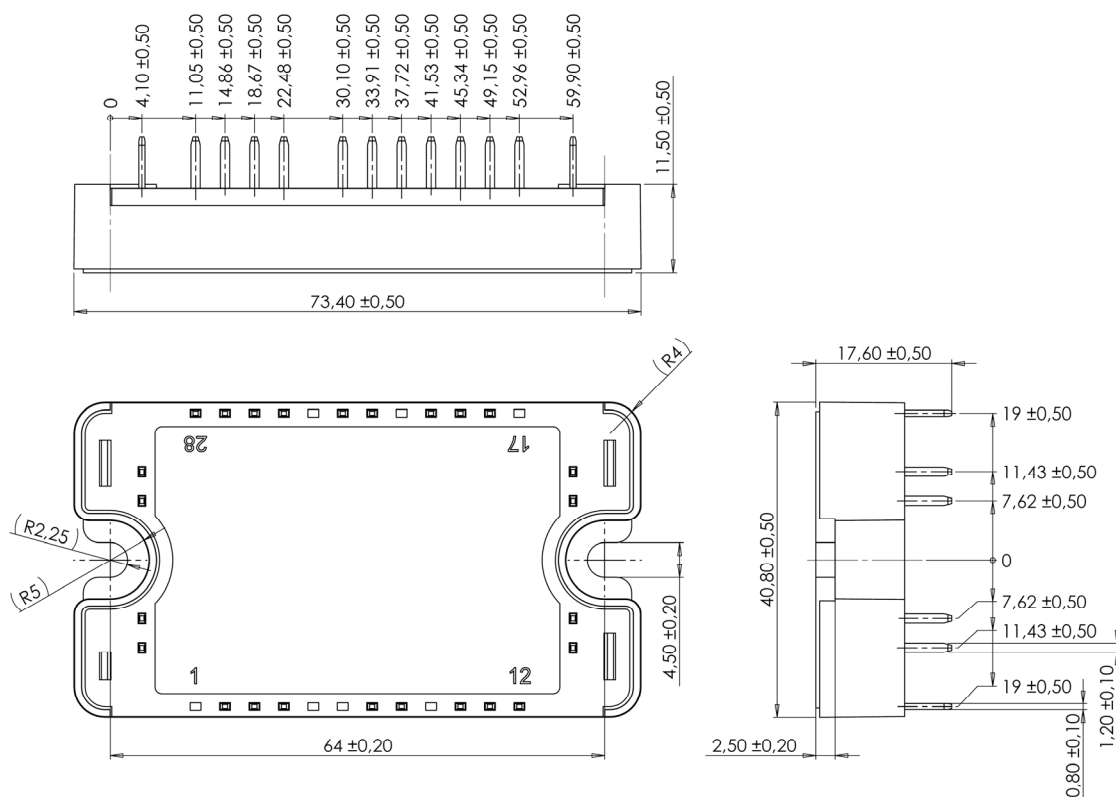
Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	MOSFET			0.32	°C/W
		Diode			0.85	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min,50/60Hz		4000			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To Heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

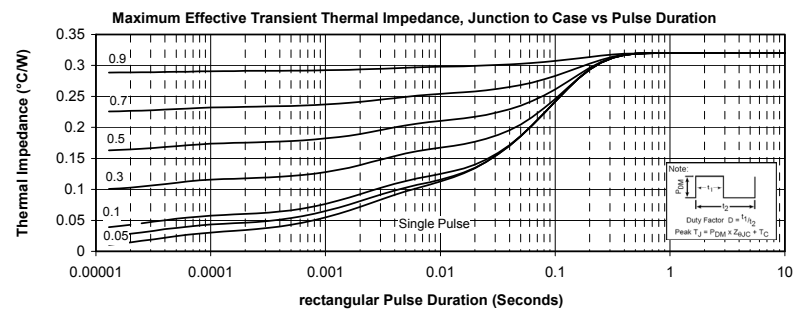
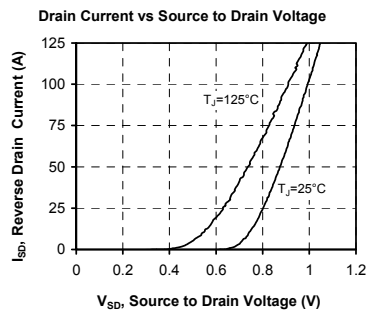
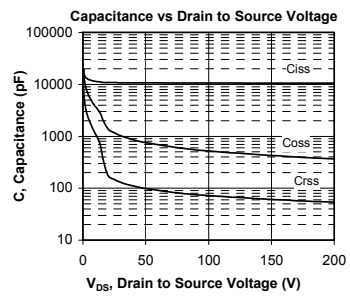
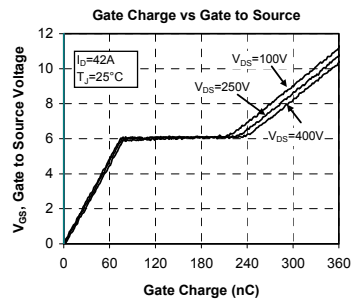
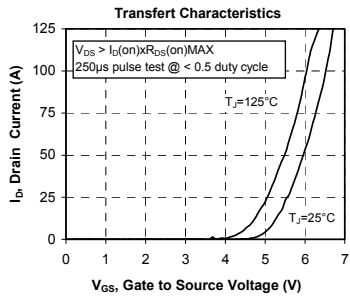
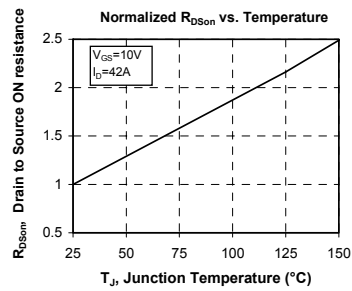
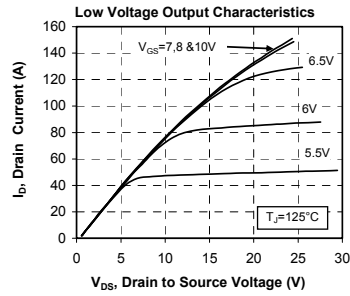
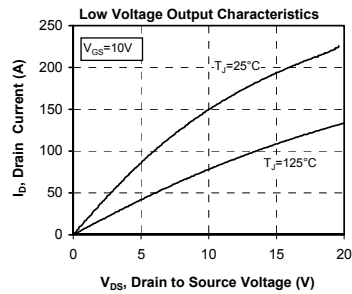
Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
ΔR ₂₅ /R ₂₅				5		%
B _{25/85}	T ₂₅ = 298.15 K			3952		K
ΔB/B		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

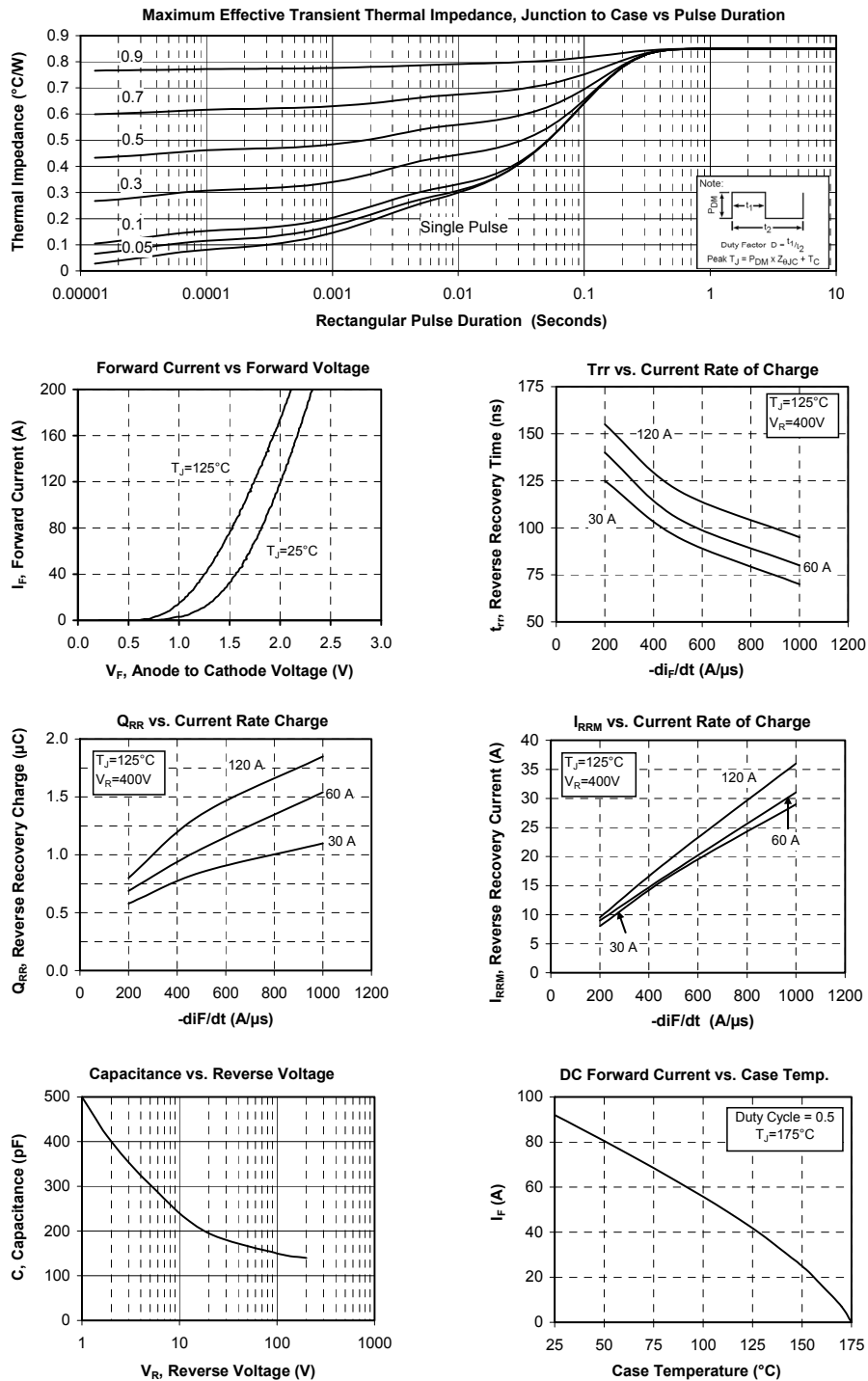
T: Thermistor temperature
R_T: Thermistor value at T

SP3 Package outline (dimensions in mm)

 See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical MOSFET Performance Curve



Typical diode Performance Curve



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